Thursday, 5th - Poster Session I
chair : P. Bouysse / co-chair : M. Prigent

G. Batistell, *SCPA non-linearity Modelling and Analysis,*

M. Bouslama, *Novel AlN/GaN HEMT Electrical Model including Trapping Effects,*

H.E. Hamoud, *A Comparative Overview of Digital Predistortion Behavioral Modeling for Multi-standards Applications,*

T.M. Martin-Guerrero, *Obtaining quasi-static models by a frequency domain extraction methodology,*

K. Mukherjee, *Investigation of the trap-limited transient response of GaN HEMTs,*

R. Pécheux, *C-doped AlN/GaN HEMTs for High efficiency mmW applications ,*

A. Piacibello, *A Ku-band Compact MMIC PA based on Stacked GaAs pHEMT cells,*

M. Salter, *An Inter-Laboratory Comparison of NVNA Measurements,*

F. Simbelie, *Nonlinear electrical modeling of MASMOS structures with a conventional 3-port topology approach,*

M.S. Mugisho, *Closed-Form Design Equations for Class-E M Power Amplifier with Isolation Circuit*

Friday, 6th - Poster Session II
chair : J. Lintignat / co-chair : S. Laurent

S. Donati Guerrieri, *A novel approach to the electro-thermal sensitivity analysis of electron devices through efficient physics-based simulations,*

A. Jarndal, *Reliable PSO Based Noise Modeling Approach Applied to GaN HEMTs,*

C. Kantana, *Comparison of GMP and DVR models,*

D. Pardo, *Development of techniques for the design of a 3.5 THz fundamental balanced Schottky mixer,*

B. Pichler, *A Robust Extraction Technique for Second Order PHD Based Behavioral Models,*

G. Polli, *A high-performance C-band integrated front end in AlGaN/GaN technology ,*

R. Quaglia, *Power and efficiency continuous modes in saturated GaN HEMT devices,*

T. Reveyrand, *Multiport conversions between S, Z, Y, h, ABCD, and T parameters,*

L. Pantoli, *An Ultra-Wideband Monolitic Active Balun,*

H.V. Hunerli, *A Methodology for Analysis of mm-Wave Transmitter Linearization Trade-offs Under Spectrum Constraints,*